

L Number	Hits	Search Text	DB	Time stamp
11	3	fluorine near5 implant\$4 same (silicon or si) near4 epitax\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 13:47
12	31	fluorine near5 implant\$4 and (silicon or si) near4 epitax\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 14:03
14	18	fluorine near5 implant\$4 and (silicon or si) near5 orientat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 14:08
16	10	implant\$4 near5 (silicon or si) near5 substrate near5 orientat\$4 and (silicon or si) near5 orientat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 14:11
17	2	implant\$4 near5 (silicon or si) near5 substrate near5 orientat\$4 and (silicon or si) near5 epitax\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 15:07
34	57	oxide near5 mask\$3 same implant\$4 near5 substrate near6 (silicon or si) and (silicon or si) near5 epitax\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 16:01
35	61	buried near5 layer same (silicon near4 substrate) near4 single adj crystal\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 16:04
36	5	buried near5 layer same (silicon near4 substrate) near4 single adj crystal\$4 near4 n\$1type	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/15 16:06
-	6	ion near4 implant\$4 same (fl or flourine or fluorine) same (silicon or si) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 13:55
-	7	ion near4 implant\$4 same (fl or flourine or fluorine) and (silicon or si) near2 layer and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:07
-	62	ion near4 implant\$4 same (defect or damage) and (silicon or si) near2 layer and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:10
-	28	ion near4 implant\$4 same (defect or damage) same (silicon or si) near2 layer and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:19
-	49	low near2 temperature same (silicon or si) near15 (epitax\$3) same (CVD or vapor near2 deposit\$4) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 14:21

-	14	low near2 temperature same (silicon or si) near15 (epitax\$3) same (CVD or vapor near2 deposit\$4) same (reduc\$3 or hydrogen or "h.sub.2" or h2) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 15:06
-	29	silane same (silicon or si) near15 (epitax\$3) same (CVD or vapor near2 deposit\$4) same (reduc\$3 or hydrogen or "h.sub.2" or h2) and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 15:07
-	23	silane same (silicon or si) near15 (epitax\$3) same (CVD or vapor near2 deposit\$4) same (reduc\$3 or hydrogen or "h.sub.2" or h2) same temperature and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 15:11
-	49	silane same (silicon or si) near15 (epitax\$3) same (reduc\$3 or hydrogen or "h.sub.2" or h2) same temperature and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 15:21
-	32	(silicon or si) near15 (epitax\$3) same (hydrogen or "h.sub.2" or h2) near10 silane same temperature and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 15:57
-	1	(substrate or wafer) same implant\$4 same orientat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 16:34
-	8	(substrate or wafer) same orientat\$4 same epitax\$4 same implant\$4 and 117/\$4.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 16:37
-	70	mask\$3 same implant\$5 same epitax\$3 near5 (silicon or si) same (damag\$3 or defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:23
-	2	mask\$3 same implant\$5 near3 (neutral or atom) same epitax\$3 near5 (silicon or si) same (damag\$3 or defect)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:25
-	24	mask\$3 same implant\$5 near3 (neutral or atom) same epitax\$3 near5 (silicon or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:30
-	2	mask\$3 same implant\$5 near3 (neutral or atom) near5 (fluorine or fl) and epitax\$3 near5 (silicon or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:32
-	9	implant\$5 near3 (neutral or atom) near5 (fluorine or fl) and epitax\$3 near5 (silicon or si)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:36
-	15	implant\$5 near3 (neutral or atom) same defect near5 densit\$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:40
-	36	implant\$5 near3 (neutral or atom) same orientat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:44

-	9	implant\$5 near3 (neutral or atom) and orientat\$4 near10 (epitax\$3) near5 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:46
-	9	implant\$5 near3 (neutral or atom) and orientat\$4 near10 (epitax\$3) near5 (si or silicon) and substrate near10 orientat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:46
-	77	implant\$5 near10 substrate and orientat\$4 near10 (epitax\$3) near5 (si or silicon) and substrate near10 orientat\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:47
-	7	implant\$5 near10 substrate near10 orientat\$4 and orientat\$4 near10 (epitax\$3) near5 (si or silicon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:48
-	1	implant\$5 near10 substrate same orientat\$4 and orientat\$4 near10 (epitax\$3) near5 (si or silicon) near10 different	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/01/14 17:49